



NPN高压开关晶体管/NPN High Switching Transistor

●特点: ■击穿电压稳定■开关速度快■安全工作区宽■符合ROHS规范

●FEATURES: ■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA ■ROHS COMPLIANT

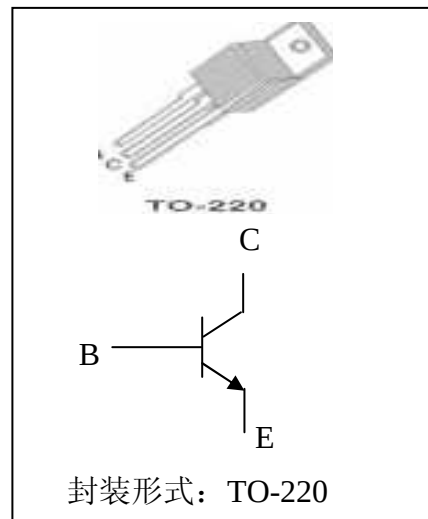
●应用: ■PC开关电源

●APPLICATION: ■PC SWITCH MODE POWER SUPPLY

●最大额定值 (TC=25℃)

●Absolute Maximum Ratings (Tc=25℃)

参数名称 PARAMETER	符号 SYMBOL	额定值 VALUE	单位 UNIT
集电极-基极电压 Collector-Base Voltage	VCBO	1100	V
集电极-发射极电压 Collector-Emitter Voltage	VCEO	700	V
发射极-基极 Emitter-Base Voltage	VEBO	9	V
集电极电流 Collector Current	IC	2	A
集电极耗散功率 Total Power Dissipation	PC	15	W
最高工作温度 Junction Temperature	Tj	150	℃
贮存温度 Storage Temperature	TsTg	-65-150	℃

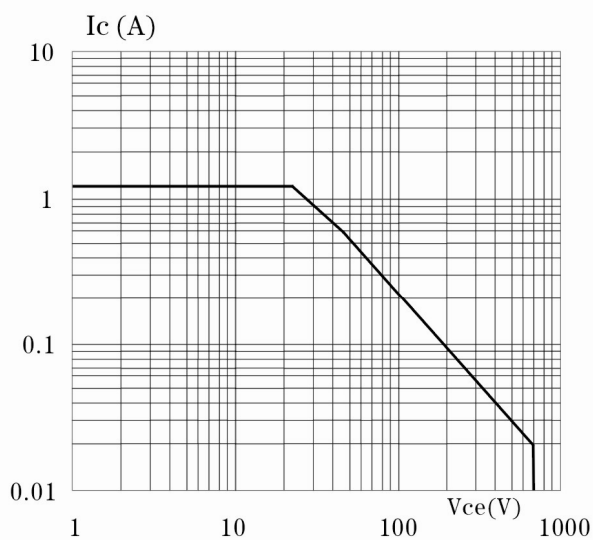


电特性 (TC=25℃)

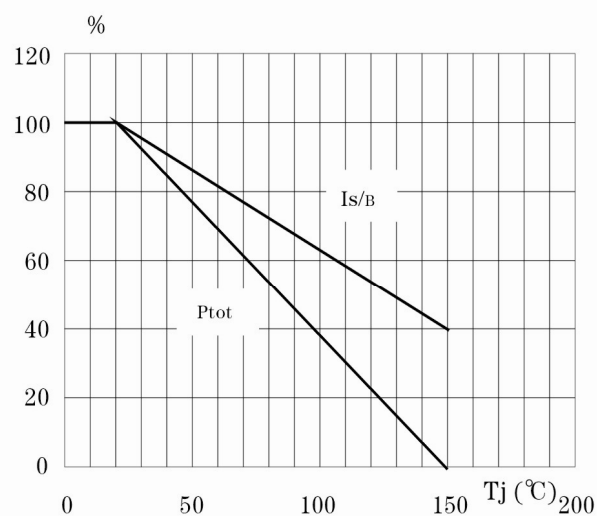
Electronic Characteristics (Tc=25℃)

参数名称 CHARACTERISTICS	符号 SYMBOL	测试条件 TEST CONDITION	最小值 MIN	最大值 MAX	单位 UNIT
集电极-基极截止电流 Collector-Base Cutoff Current	ICBO	VCB=1100V		5	uA
集电极-发射极截止电流 Collector-Emitter Cutoff Current	ICEO	VCE=700V, IB=0		10	uA
集电极-发射极电压 Collector-Emitter Voltage	VCEO	IC=10mA, IB=0	700		V
发射极-基极电压 Collector-Base Voltage	VEBO	IE=1mA, IC=0	9		V
集电极-发射极饱和压降 Collector-Emitter Saturation Voltage	Vcesat	IC=1.0A, IB=0.20A		0.85	V
		IC=2.0A, IB=0.5A		2	V
发射极-基极饱和压降Base-Emitter Saturation Voltage	Vbesat	IC=1.0A, IB=0.2A		1.2	V
电流放大倍数 DC Current Gain	Hfe	VCE=5V, IC=1mA	8		
		VCE=5V, IC=0.5A	20	30	
		VCE=5V, IC=1.2A	6		
贮存时间 Storage Time	ts	VCC=5V IC=0.5A (UI9600)	3.0	6.0	us
下降时间 falling time	tf			4.0	

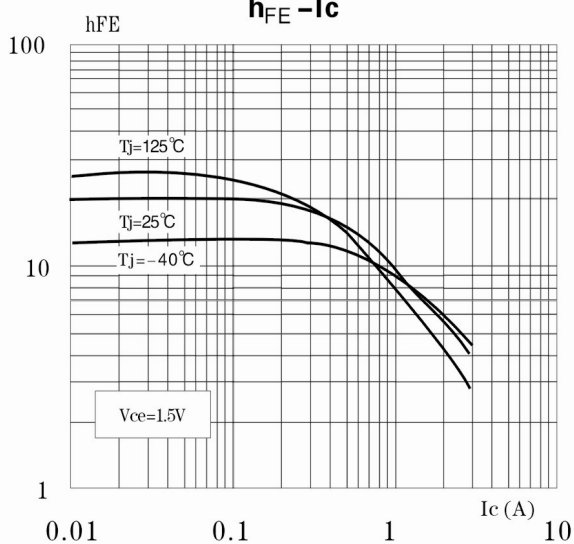
SOA(DC)



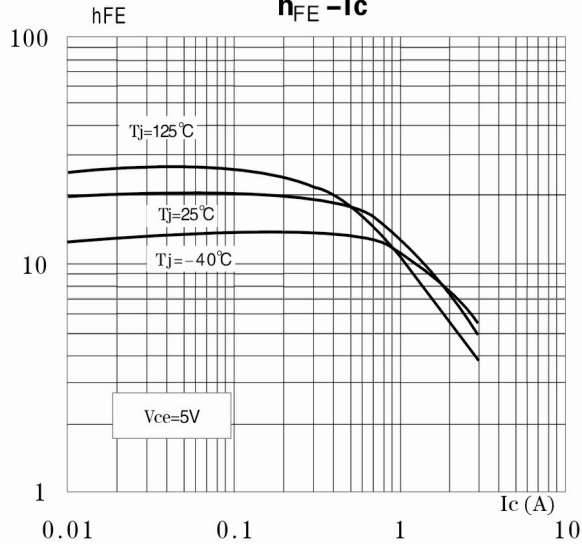
$P_c \propto T_j$



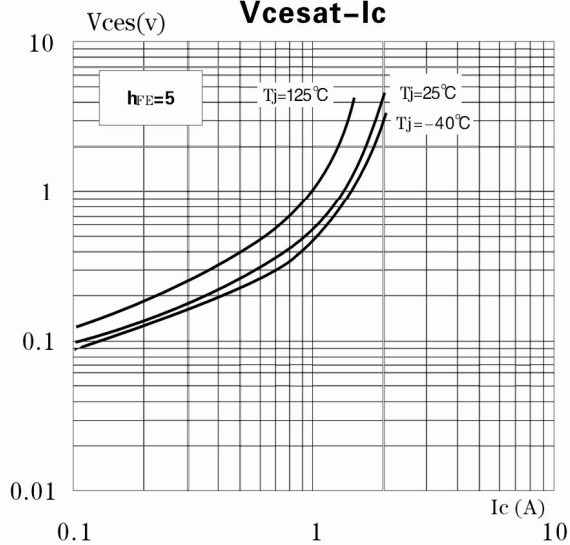
$h_{FE} - I_c$



$h_{FE} - I_c$



$V_{cesat} - I_c$



$V_{besat} - I_c$

